Analog Multiplexer/ Demultiplexer

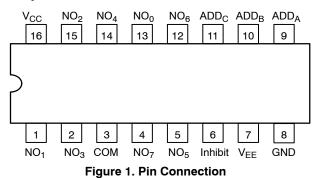
TTL Compatible, Single-Pole, 8-Position Plus Common Off

The NLAST4051 is an improved version of the MC14051 and MC74HC4051 fabricated in sub–micron Silicon Gate CMOS technology for lower $R_{DS(on)}$ resistance and improved linearity with low current. This device may be operated either with a single supply or dual supply up to $\pm 3~V$ to pass a 6 V_{PP} signal without coupling capacitors.

When operating in single supply mode, it is only necessary to tie V_{EE} , pin 7 to ground. For dual supply operation, V_{EE} is tied to a negative voltage, not to exceed maximum ratings. Translation is provided in the device, the Address and Inhibit are standard TTL level compatible. For CMOS compatibility see NLAS4051. Pin for pin compatible with all industry standard versions of '4051.'

Features

- Improved R_{DS(on)} Specifications
- Pin for Pin Replacement for MAX4051 and MAX4051A
 - One Half the Resistance Operating at 5.0 V
- Single or Dual Supply Operation
 - Single 3.0 5.0 V Operation, or Dual ±3 V Operation
 - With V_{CC} of 3.0 to 3.3 V, Device Can Interface with 1.8 V Logic. No Translators Needed
 - Address and Inhibit Logic are Over–Voltage Tolerant and May Be Driven Up +6 V Regardless of $V_{\rm CC}$
- Address and Inhibit Pins Standard TTL Compatible
 - Greatly Improved Noise Margin Over MAX4051 and MAX4051A
 - True TTL Compatibility $V_{IL} = 0.8 \text{ V}, V_{IH} = 2.0 \text{ V}$
- Improved Linearity Over Standard HC4051 Devices
- Space Saving TSSOP Package
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

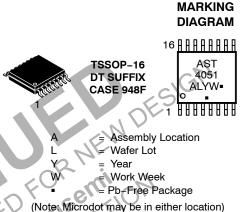


(Top View)



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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

TRUTH TABLE

Inhibit		Address		ON SWITCHES*
	С	В	Α	
1	X don't care	X don't care	X don't care	All switches open
0	0	0	0	COM-NO ₀
0	0	0	1	COM-NO ₁
0	0	1	0	COM-NO ₂
0	0	1	1	COM-NO ₃
0	1	0	0	COM-NO ₄
0	1	0	1	COM-NO ₅
0	1	1	0	COM-NO ₆
0	1	1	1	COM-NO ₇

^{*}NO and COM pins are identical and interchangeable. Either may be considered an input or output; signals pass equally well in either direction.

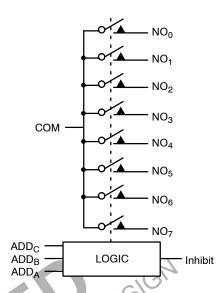


Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	P	arameter	Value	Unit
V _{EE}	Negative DC Supply Voltage	(Referenced to GND)	-7.0 to +0.5	V
V _{CC}	Positive DC Supply Voltage (Note 1)	(Referenced to GND) (Referenced to $V_{\rm EE}$)	-0.5 to +7.0 -0.5 to +7.0	V
V _{IS}	Analog Input Voltage		V_{EE} =0.5 to V_{CC} +0.5	V
V _{IN}	Digital Input Voltage	(Referenced to GND)	-0.5 to 7.0	V
I	DC Current, Into or Out of Any Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for	r 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
θ_{JA}	Thermal Resistance		164	°C/W
P_{D}	Power Dissipation in Still Air		450	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% - 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 > 1000	V
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. The absolute value of $V_{CC} \pm |V_{EE}| \le 7.0$. 2. Tested to EIA/JESD22–A114–A.
- 3. Tested to EIA/JESD22-A115-A.
- Tested to JESD22-C101-A. 4.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{EE}	Negative DC Supply Voltage	(Referenced to GND)	-5.5	GND	V
V _{CC}	Positive DC Supply Voltage	(Referenced to GND) (Referenced to V _{EE})	2.5 2.5	5.5 6.6	V
V _{IS}	Analog Input Voltage		V _{EE}	V _{CC}	V
V _{IN}	Digital Input Voltage	(Note 6) (Referenced to GND)	0	5.5	V
T _A	Operating Temperature Range, All Package Types		-55	125	°C
t _r , t _f	Input Rise/Fall Time (Channel Select or Enable Inputs)	V_{CC} = 3.0 V \pm 0.3 V V_{CC} = 5.0 V \pm 0.5 V	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

			Vcc	Guara	nteed Lin	nit	
Symbol	Parameter	Condition	V	-55 to 25°C	≤85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage, Address or Inhibit Inputs		3.0 4.5 5.5	1.6 2.0 2.0	1.6 2.0 2.0	1.6 2.0 2.0	V
V _{IL}	Maximum Low-Level Input Voltage, Address or Inhibit Inputs		3.0 4.5 5.5	0.5 0.8 0.8	0.5 0.8 0.8	0.5 0.8 0.8	V
I _{IN}	Maximum Input Leakage Current, Address or Inhibit Inputs	V _{IN} = 6.0 or GND	0 V to 6.0 V	P \$0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	Address or Inhibit and V _{IS} = V _{CC} or GND	6.0	4.0	40	80	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DC ELECTRICAL CHARACTERISTICS - Analog Section

				V _{EE}	Guara	nit		
Symbol	Parameter	Test Conditions	V _{CC}	VEE	-55 to 25°C	≤85°C	≤125°C	Unit
R _{ON}	Maximum "ON" Resistance	$V_{IN} = V_{IL}$ or V_{IH} $V_{IS} = (V_{EE} \text{ to } V_{CC})$ $ I_S = 10 \text{ mA}$ (Figures 4 thru 9)	3.0 4.5 3.0	0 0 -3.0	86 37 26	108 46 33	120 55 37	Ω
ΔR _{ON}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Pack- age	$ \begin{aligned} V_{IN} &= V_{IL} \text{ or } V_{IH,} & V_{IS} &= 2.0 \text{ V} \\ V_{IS} &= 3.0 \text{ V} \\ I_S &= 10 \text{ mA}, & V_{IS} &= 2.0 \text{ V} \end{aligned} $	3.0 4.5 3.0	0 0 -3.0	15 13 10	20 18 15	20 18 15	Ω
Rflat _(ON)	ON Resistance Flatness	V _{COM} = 1, 2, 3.5 V V _{COM} = 2, 0, 2 V	4.5 3.0	3.0	4 2	4 2	5 3	Ω
I _{NC(OFF)} I _{NO(OFF)}	Maximum Off-Channel Leakage Current	Switch Off $V_{IN} = V_{IL}$ or V_{IH} $V_{IO} = V_{CC} - 1.0$ V or $V_{EE} + 1.0$ V (Figure 17)	6.0 3.0	0 -3.0	0.1 0.1	5.0 5.0	100 100	nA
I _{COM(ON)}	Maximum On-Channel Leakage Current, Channel-to-Channel	Switch On $V_{IO} = V_{CC} - 1.0 \text{ V or } V_{EE} + 1.0 \text{ V}$ (Figure 17)	6.0 3.0	0 -3.0	0.1 0.1	5.0 5.0	100 100	nA

^{6.} Unused digital inputs may not be left open. All digital inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

AC CHARACTERISTICS (Input $t_r = t_f = 3 \text{ ns}$)

						Guaran		nteed Limit		
			V _{CC}	V _{EE}	-55 to	25°C				
Symbol	Parameter	Test Conditions	V	V	Min	Тур*	≤85°C	≤125°C	Unit	
t _{BBM}	Minimum Break-Before-Make Time	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = V_{CC}$	3.0 4.5	0.0 0.0	1.0 1.0	6.5 5.0		-	ns	
		$R_L = 300 \Omega, C_L = 35 pF$ (Figure 19)	3.0	-3.0	1.0	3.5	_	-		

^{*}Typical Characteristics are at 25°C.

AC CHARACTERISTICS (C_L = 35 pF, Input t_r = t_f = 3 ns)

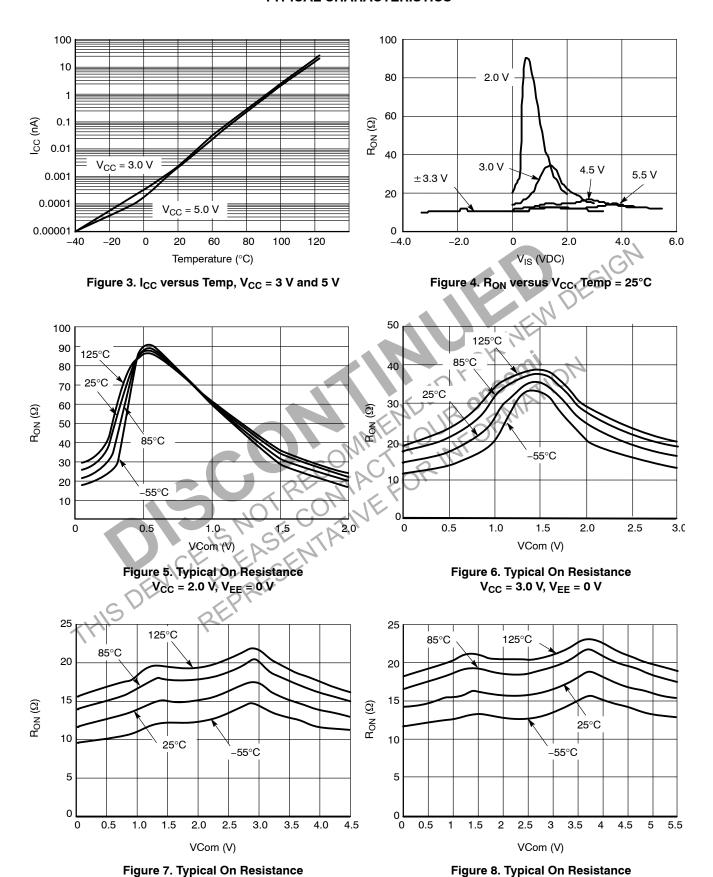
				Guaranteed Limit							
		v _{cc}	V _{EE}	_	55 to 25	°C	≤8	35°C	≤1	25°C	
Symbol	Parameter	V	VEE	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{TRANS}	Transition Time (Address Selection Time) (Figure 18)	2.5 3.0 4.5 3.0	0 0 0 -3.0			40 28 23 23		45 30 25 25	15	50 35 30 28	ns
t _{ON}	Turn-on Time (Figures 14, 15, 20, and 21) Enable to N _O or N _C	2.5 3.0 4.5 3.0	0 0 0 -3.0			40 28 23 23		45 30 25 25		50 35 30 28	ns
t _{OFF}	Turn-off Time (Figures 14, 15, 20, and 21) Enable to N _O or N _C	2.5 3.0 4.5 3.0	0 0 0 -3.0			40 28 23 23	nse	45 30 25 25	M	50 35 30 28	ns

	Typical @ 25°C, V _{CC} = 5.0 V	
C _{IN}	Maximum Input Capacitance, Select Inputs 8	pF
C _{NO} or C _{NC}	Analog I/O 10	
C _{COM}	Common I/O 10	
C _(ON)	Feedthrough 1.0	

ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)

	Mo br	ESV	v _{cc}	V _{EE}	Тур	
Symbol	Parameter	Condition	V	V	25°C	Unit
BW	Maximum On-Channel Bandwidth or Minimum Frequency Response	V _{IS} = ½ (V _{CC} - V _{EE}) Source Amplitude = 0 dBm (Figures 10 and 22)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	80 90 95 95	MHz
V _{ISO}	Off-Channel Feedthrough Isolation	f = 100 kHz; V_{IS} = $1\!\!/_{\!\!2}$ (V_{CC} – V_{EE}) Source = 0 dBm (Figures 12 and 22)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	-93 -93 -93 -93	dB
V _{ONL}	Maximum Feedthrough On Loss	$V_{IS} = \frac{1}{2} (V_{CC} - V_{EE})$ Source = 0 dBm (Figures 10 and 22)	3.0 4.5 6.0 3.0	0.0 0.0 0.0 -3.0	-2 -2 -2 -2	dB
Q	Charge Injection	V_{IN} = V_{CC} to $V_{EE,}$ f_{IS} = 1 kHz, t_r = t_f = 3 ns R_{IS} = 0 $\Omega,$ C_L = 1000 pF, Q = C_L * ΔV_{OUT} (Figures 16 and 23)	5.0 3.0	0.0 -3.0	9.0 12	pC
THD	Total Harmonic Distortion THD + Noise	f_{IS} = 1 MHz, R_L = 10 K Ω , C_L = 50 pF, V_{IS} = 5.0 V_{PP} sine wave V_{IS} = 6.0 V_{PP} sine wave (Figure 13)	6.0 3.0	0.0 -3.0	0.10 0.05	%

TYPICAL CHARACTERISTICS



 V_{CC} = 5.5 V, V_{EE} = 0 V

 V_{CC} = 4.5 V, V_{EE} = 0 V

TYPICAL CHARACTERISTICS

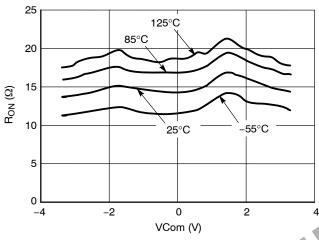


Figure 9. Typical On Resistance $V_{CC} = 3.3 \text{ V}, V_{EE} = -3.3 \text{ V}$

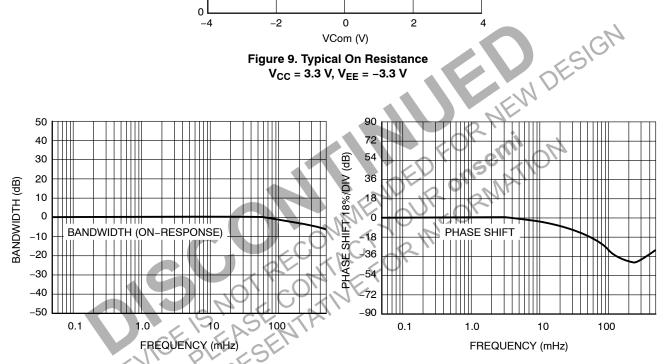


Figure 10. Bandwidth

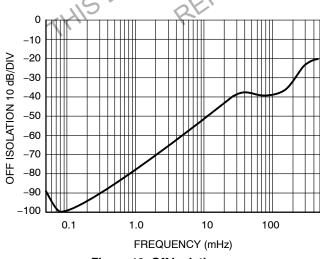


Figure 12. Off Isolation

Figure 11. Phase Shift

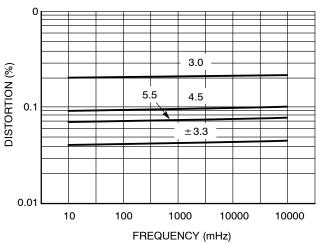
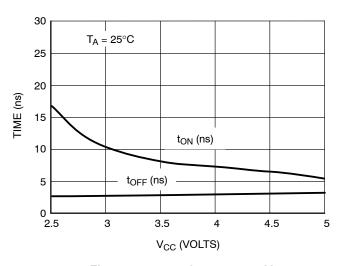


Figure 13. Total Harmonic Distortion

TYPICAL CHARACTERISTICS



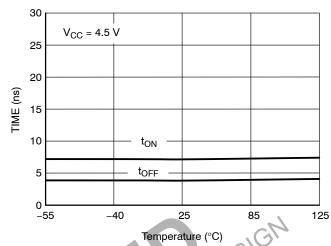
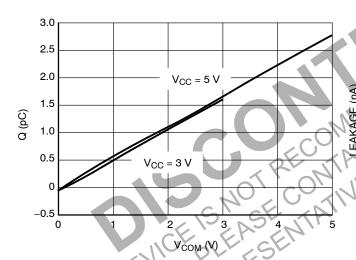


Figure 14. t_{ON} and t_{OFF} versus V_{CC}

Figure 15. t_{ON} and t_{OFF} versus Temp



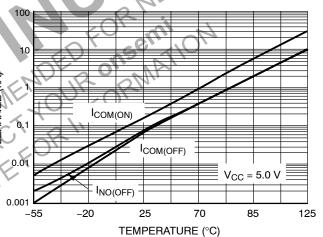


Figure 16. Charge Injection versus COM Voltage

Figure 17. Switch Leakage versus Temperature

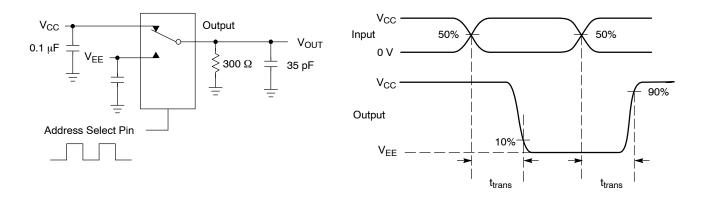
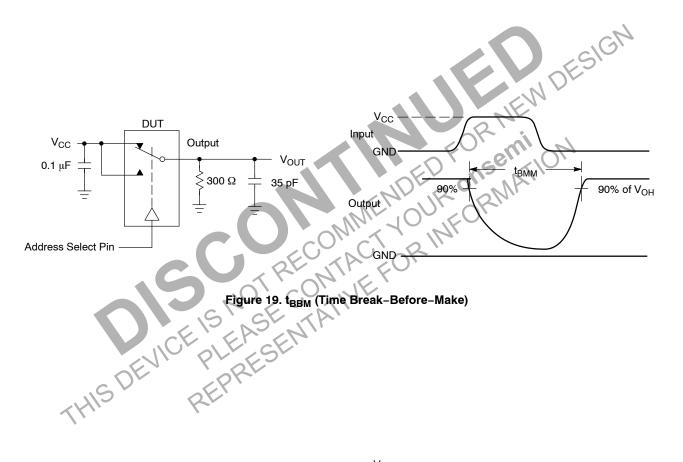


Figure 18. Channel Selection Propagation Delay



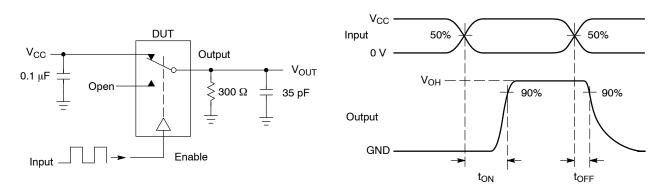


Figure 20. t_{ON}/t_{OFF}

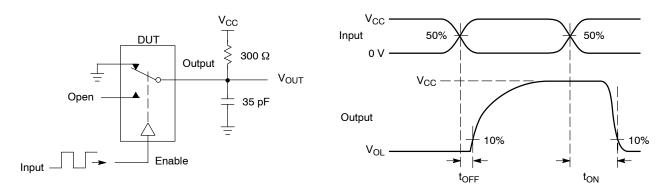
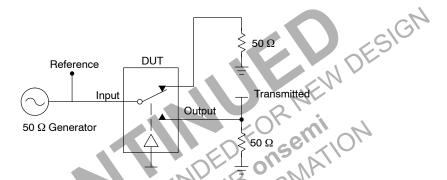


Figure 21. t_{ON}/t_{OFF}



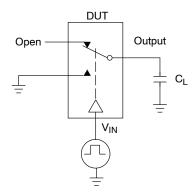
Channel switch Address and Inhibit/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. $V_{\rm ISO}$, Bandwidth and $V_{\rm ONL}$ are independent of the input signal direction.

$$V_{ISO} = Off Channel Isolation = 20 Log \left(\frac{V_{QUT}}{V_{IN}}\right)$$
 for V_{IN} at 100 kHz

 $V_{ONL} = On Channel Loss = 20 Log \left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz to 50 MHz

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

Figure 22. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}



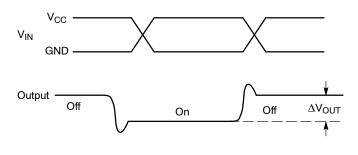
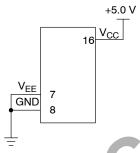


Figure 23. Charge Injection: (Q)

TYPICAL OPERATION





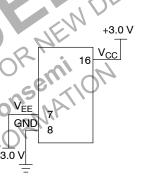


Figure 25. Dual Supply $V_{CC} = 3.0 \text{ V}, V_{EE} = -3.0 \text{ V}$

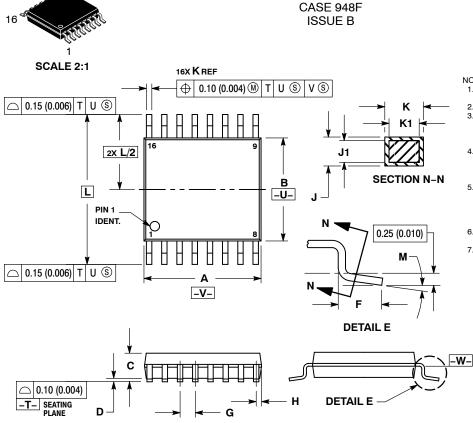
ORDERING INFORMATION

Device	Package	Shipping [†]
NLAST4051DTR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel
NLVAST4051DTR2G*	TSSOP-16 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.





TSSOP-16 WB

DATE 19 OCT 2006

NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252	BSC
М	0 °	8°	0°	8 °

RECOMMENDED SOLDERING FOOTPRINT*

7.06 ٦ 1 0.65 **PITCH** 16X 0.36 1.26 **DIMENSIONS: MILLIMETERS**

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TSSOP-16		PAGE 1 OF 1

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